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(54) **SEMICONDUCTOR DEVICES**

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(57) **ABSTRACT**

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A semiconductor device includes: an active pattern on a substrate; a gate structure in an upper portion of the active pattern; a bit line structure on the active pattern; a spacer structure on a sidewall of the bit line structure, the spacer structure including an insulating material; and a lower contact plug on a portion of the active pattern adjacent to the bit line structure, the lower contact plug contacting the spacer structure, wherein the spacer structure includes a layer having at least two curves and a vertex disposed between and contacting the two curves.

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